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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

November 2025

FQB1P50

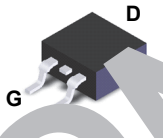
P-Channel QFET® MOSFET
- 500 V, - 1.5 A, 10.5 Ω

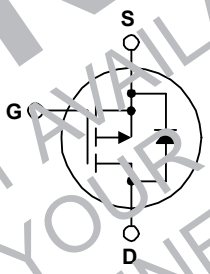
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- - 1.5 A, - 500 V, $R_{DS(on)}$ = 10.5 Ω (M...) @ $V_{G...}$ - 10 V, I_D = - 0.75 A
- Low Gate Charge (Typ. 1... nC)
- Low Crss (Typ. 6.0 pF)
- 100% Avalanche ...sted
- RoHS Com...nt





Absolu... Maxi...um Ratings

T_C = 25°C unless o...herwise noted

Symbol	Parameter		FQB1P50TM	Unit
V...	Drain-Source Voltage		-500	V
I_D	Drain Current - Continuous (T_C = 25°C)		-1.5	A
	- Continuous (T_C = 10...°C)		-0.95	A
I_{DM}	Drain Current - Pulsed	(Note 1)	-6.0	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	110	mJ
I_{AR}	Avalanche Current	(Note 1)	-1.5	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	6.3	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-4.5	V/ns
P_D	Power Dissipation (T_A = 25°C) *		3.13	W
	Power Dissipation (T_C = 25°C)		63	W
	- Derate above 25°C		0.51	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQB1P50TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	1.98	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (1 in^2 pad of 2 oz copper), Max.	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQB1P50	FQB1P50TM	D2-PAK	330mm	24mm	800

Elerical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = -250 µA	-500	--	--	
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = -250 µA, Referenced to 25°C	--	-	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -500 V, V_{GS} = 0 V	--		-1	µA
		V_{DS} = -400 V, T_C = 125°C	--		-10	
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = 30 V, V_{DS} = 0 V	--	--	1	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250 µA		--	-5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = -10 V, I_D = -0.75 A	--	8.0	10.5	Ω
g_{FS}	Forward Transconductance	V_{DS} = -50 V, I_D = -0.75 A	--	1.26	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -25 V, V_{GS} = 0 V,	--	270	350	pF
C_{oss}	Output Capacitance	f = 1.0 MHz	--	40	50	pF
C_{rss}	Reverse Transfer Capacitance		--	6.5	8.0	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = -250 V, I_D = -1.5 A,	--	9.0	30	ns
t_r	Turn-On Rise Time	R_G = 25 Ω	--	25	60	ns
$t_{d(off)}$	Turn-Off Delay Time		--	27	65	ns
t_f	Turn-Off Fall Time	(Note 4)	--	30	70	ns
Q_g	Total Gate Charge	V_{DS} = -400 V, I_D = -1.5 A,	--	11	14	nC
Q_{gs}	Gate-Source Charge	V_{GS} = -10 V	--	2.0	--	nC
Q_{gd}	Gate-Drain Charge	(Note 4)	--	5.6	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	-1.5	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-6.0	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = -1.5 A	--	--	-5.0	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = -1.5 A,	--	200	--	ns
Q_{rr}	Reverse Recovery Charge	dI_F / dt = 100 A/µs	--	0.7	--	µC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 88mH, I_{AS} = -1.5A, V_{DD} = -50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ -1.5A, di/dt ≤ 200A/µs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially independent of operating temperature

Typical Characteristics

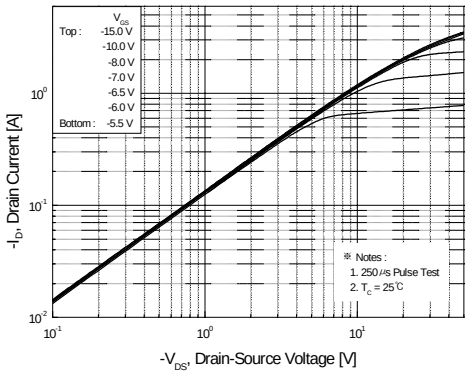


Figure 1. On-Region Characteristics

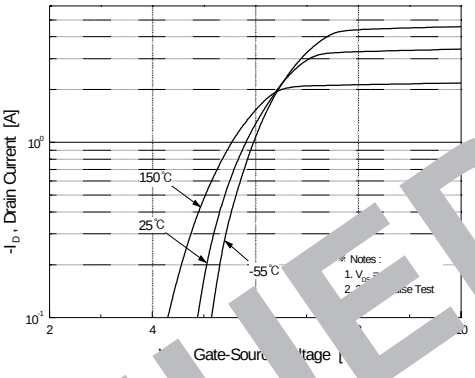


Figure 2. Transfer Characteristics

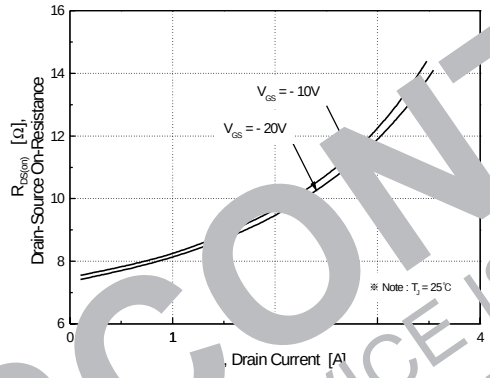


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

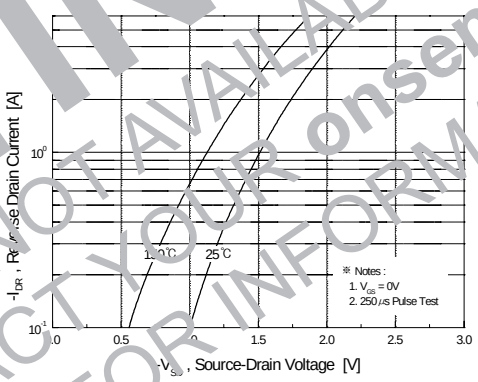


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

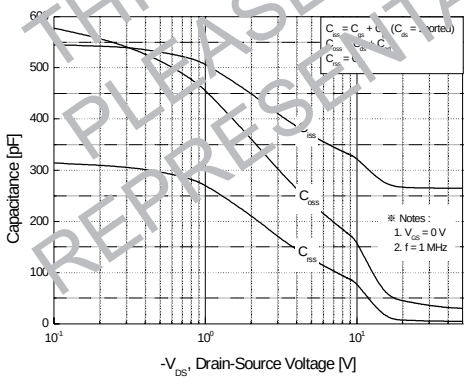


Figure 5. Capacitance Characteristics

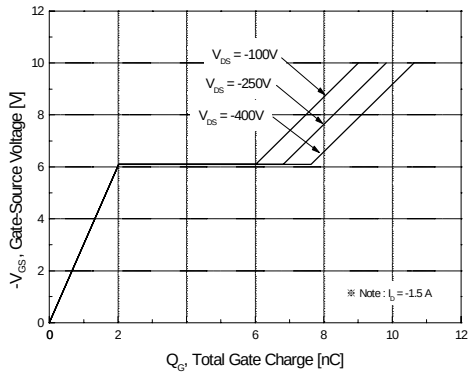


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

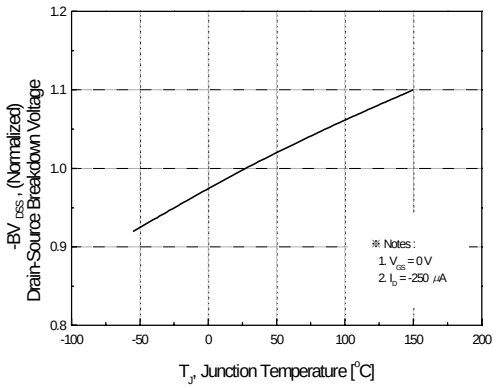


Figure 7. Breakdown Voltage Variation vs. Temperature

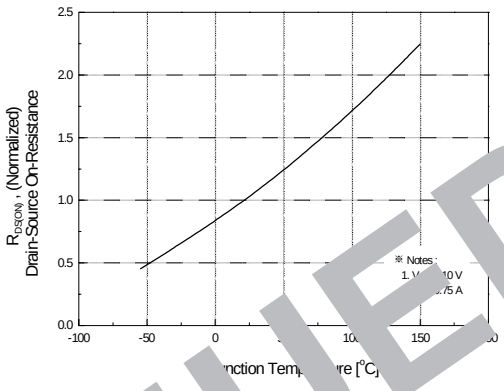


Figure 8. On-Resistance Variation vs. Temperature

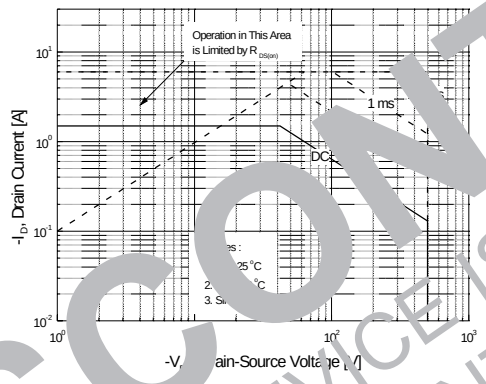


Figure 9. Maximum Safe Operating Area

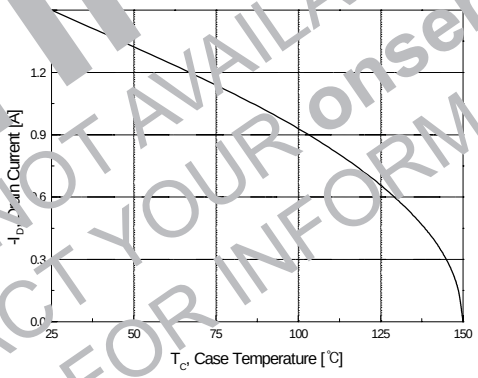


Figure 10. Maximum Drain Current vs. Case Temperature

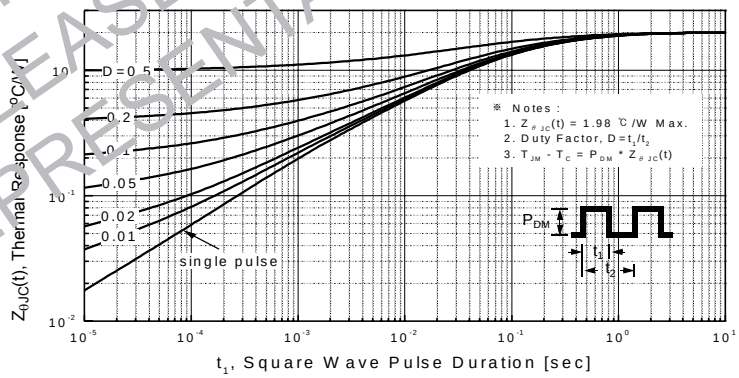


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

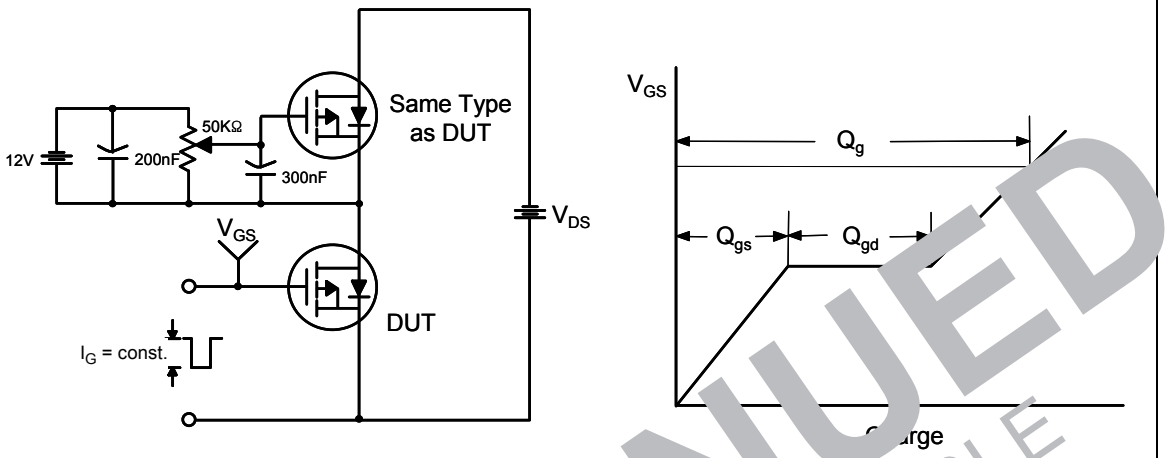


Figure 13. Resistive Switching Test Circuit & Waveforms

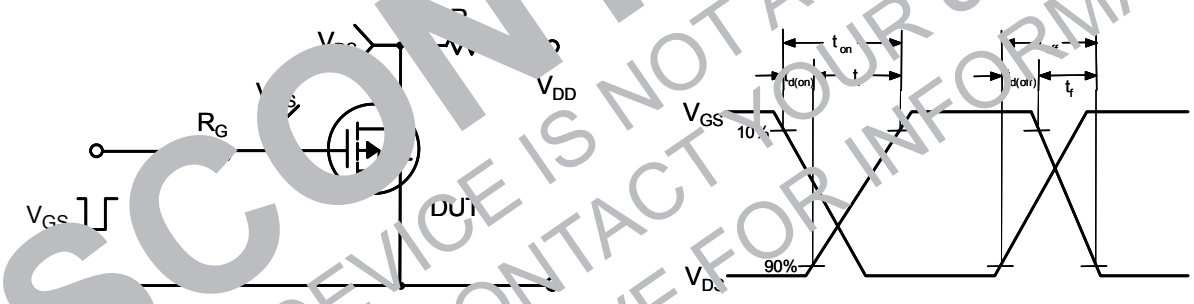


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

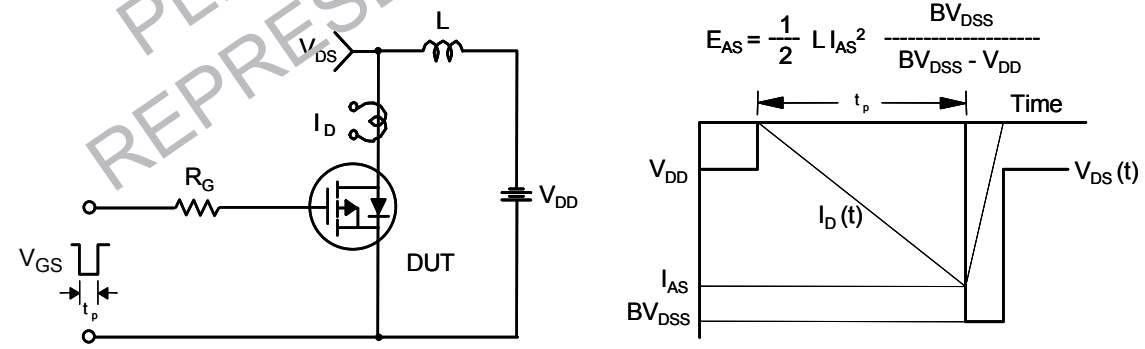
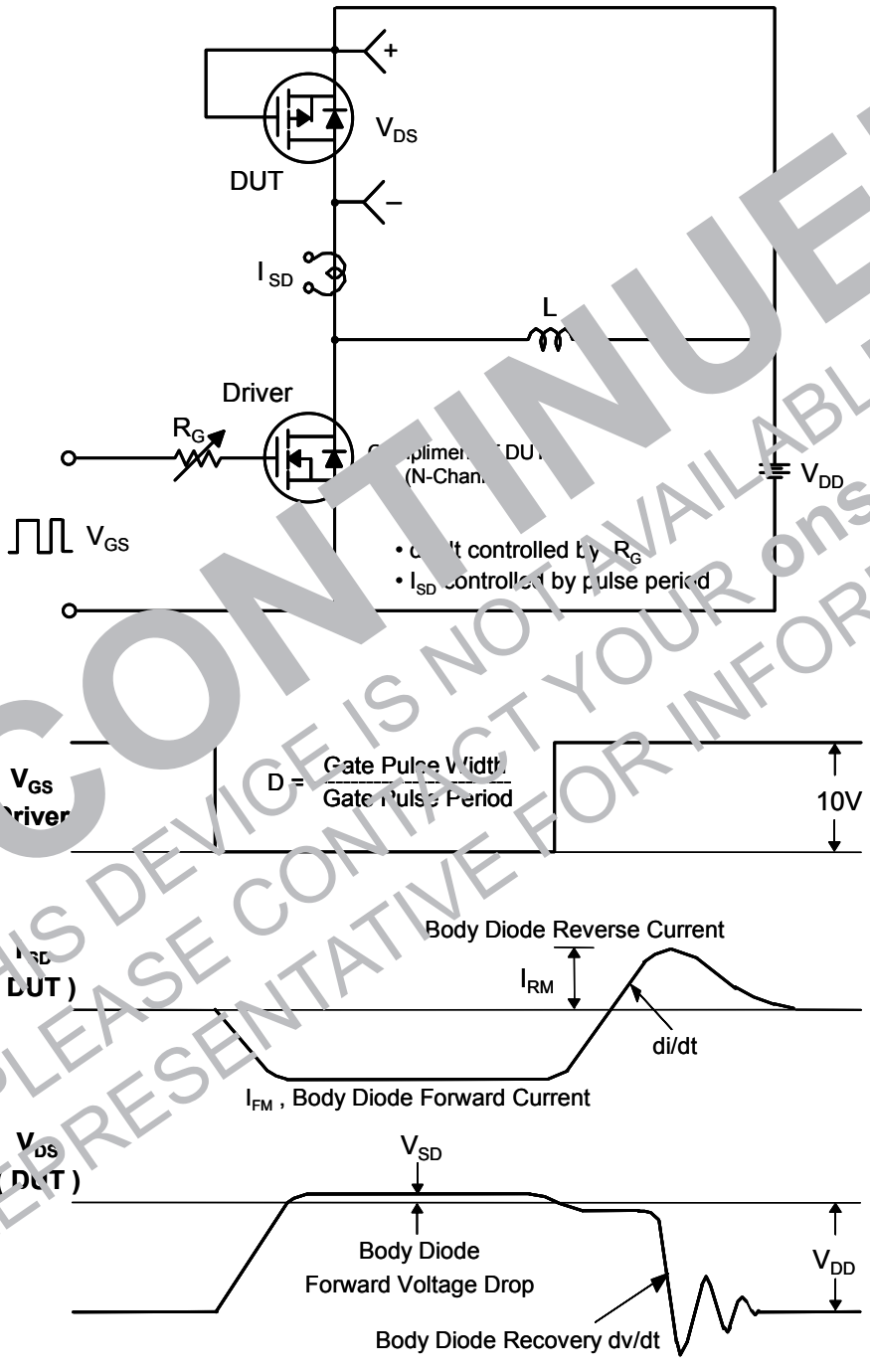
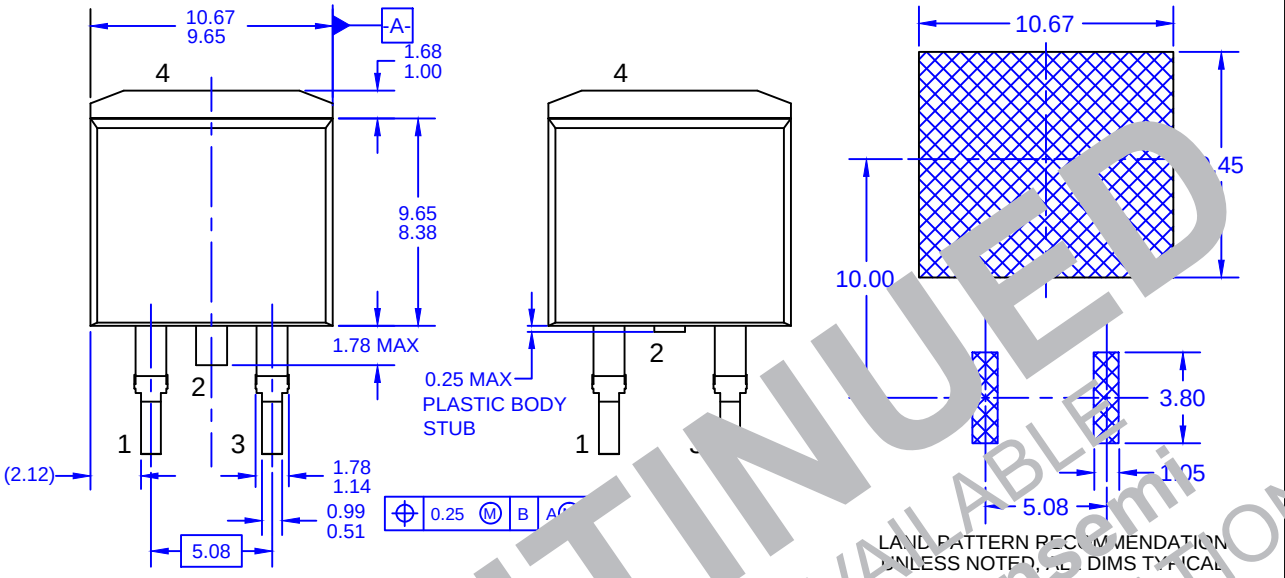


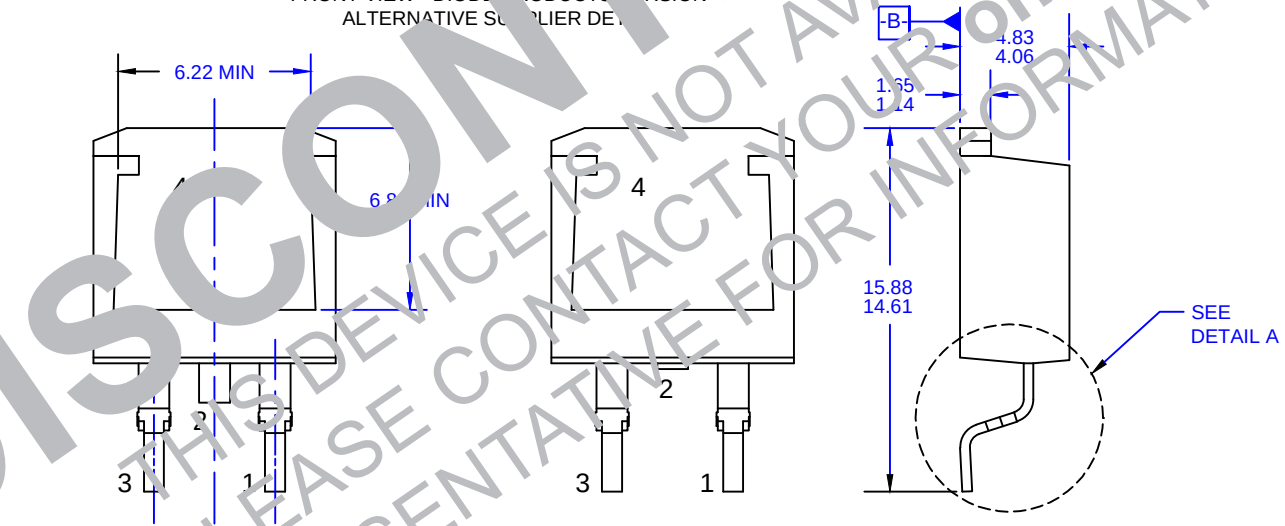
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



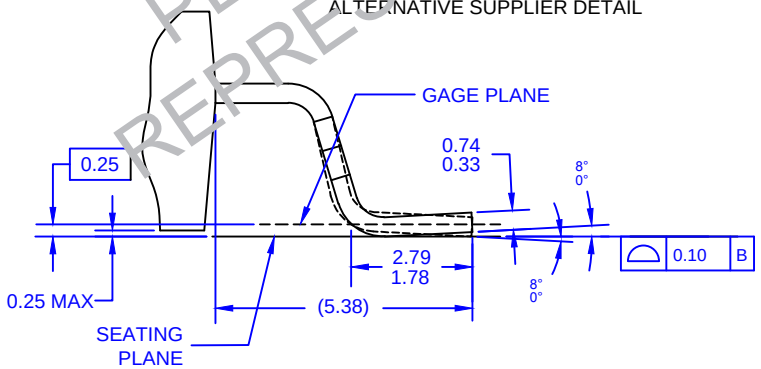


FRONT VIEW - DIODE PRODUCTS VERSION
ALTERNATIVE SUPPLIER DETAIL

LAND PATTERN RECOMMENDATION
UNLESS NOTED, ALL DIMS TYPICAL



BACK VIEW - DIODE PRODUCTS VERSION
ALTERNATIVE SUPPLIER DETAIL



DETAIL A, ROTATED 90°
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED
A) ALL DIMENSIONS ARE IN MILLIMETERS.
B) REFERENCE JEDEC, TO-263, VARIATION AB.
C) DIMENSIONING AND TOLERANCING PER DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.
D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N
F) FILENAME: TO263A02REV8

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